ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE373 (NPN) & NTE374 (PNP)
Silicon Complementary Transistors
Audio Amplifier, Driver

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 180V

Collector–Emitter Voltage, V_{CEO} 160V

Emitter–Base Voltage, V_{EBO} 5V

Collector Current, I_C

- Continuous 1.5A
- Peak 3A

Collector Power Dissipation, P_D

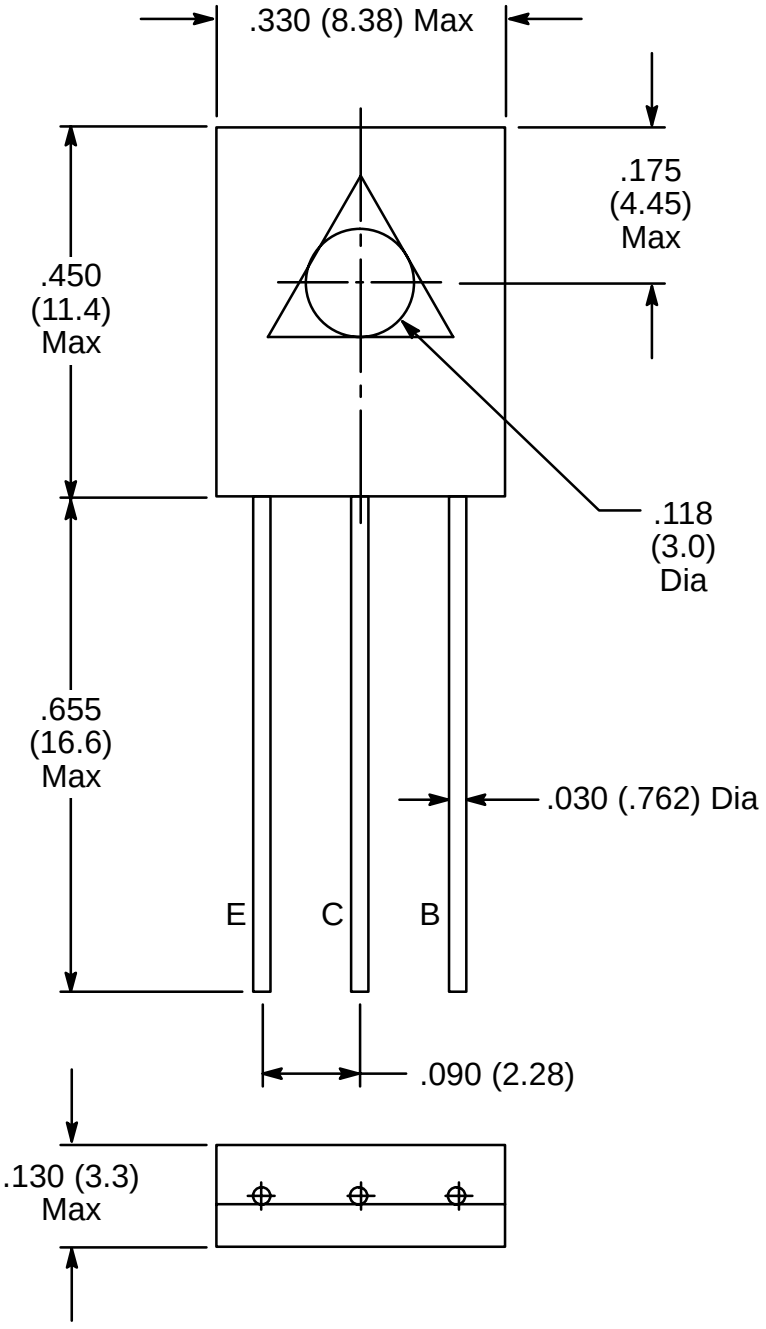
- T_A = +25°C 1W
- T_C = +25°C 20W

Operating Junction Temperature, T_J . . . . . +150°C

Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 1mA, I_E = 0	180	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, R_{BE} = ∞	160	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 1mA, I_C = 0	5	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 160V, I_E = 0	–	–	10	µA
DC Current Gain	h_{FE1}	V_{CE} = 5V, I_C = 150mA	60	–	200	
	h_{FE2}	V_{CE} = 5V, I_C = 500mA	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	–	–	1	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 150mA	–	–	1.5	V
Transistion Frequency	f_T	V_{CE} = 5V, I_C = 500mA	–	140	–	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	14	–	pF


.330 (8.38) Max
.175
(4.45)
Max
.450
(11.4)
Max
.118
(3.0)
Dia
.655
(16.6)
Max
.030 (.762) Dia
E
C
B
.090 (2.28)
.130 (3.3)
Max